

NTE156 General Purpose Silicon Rectifier

Features:

- Low Leakage
- Low Forward Voltage Drop
- High Current Capability

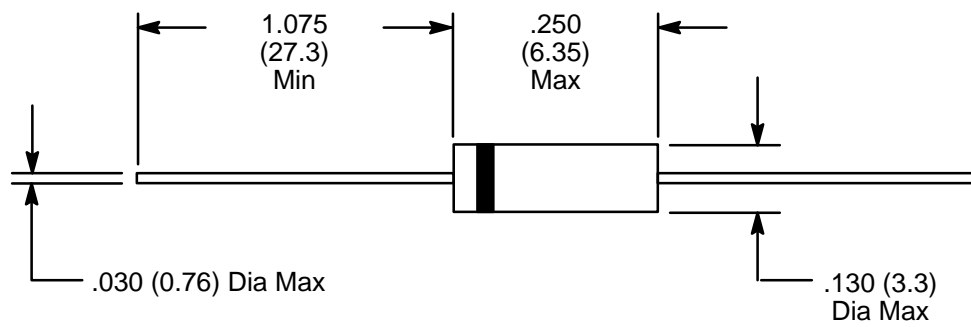
Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%)

Peak Repetitive Reverse Voltage, V_{RRM}	1000V
DC Blocking Voltage, V_R	1000V
RMS Reverse Voltage, $V_{R(RMS)}$	700V
Average Rectified Forward Current, I_O (.375" (9.5mm) lead length, $T_A = +50^\circ\text{C}$)	2A
Non-Repetitive Peak Surge Current, I_{FSM} (8.3ms single half sine-wave superimposed on rated load)	70A
Operating Junction Temperature Range, T_J	-65° to $+175^\circ\text{C}$
Storage Temperature Range, T_{stg}	-65° to $+175^\circ\text{C}$
Typical Thermal Resistance, Junction-to-Ambient, R_{thJA}	50°C/W

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage Drop	V_F	$I_F = 2A$	–	–	1.1	V
Maximum Reverse Current	I_R	$V_{RRM} = 1000V, T_J = +25^\circ\text{C}$	–	–	5.0	μA
		$V_{RRM} = 1000V, T_J = +100^\circ\text{C}$	–	–	50	
Maximum Full-Cycle Average Reverse Current	$I_{R(AV)}$	$T_L +75^\circ\text{C}, .375 (9.5) \text{ leads}$	–	–	30	μA
Typical Junction Capacitance	C_j	Note 1	–	40	–	pF

Note 1. Measured at 1MHz and applied reverse voltage of 4.0 volts.



Color Band Denotes Cathode